

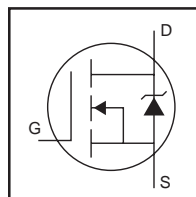
International
IR Rectifier

HEXFET® Power MOSFET Die in Wafer Form

PD - 93777

IRFC2907B

- 100% Tested at Probe
- Available in Tape and Reel, Chip Pack, Sawn on Film and Gel Pack**
- Ultra Low On-Resistance



75V
$R_{DS(on)} = 2.5m\Omega$ (typ.)***
6" Wafer

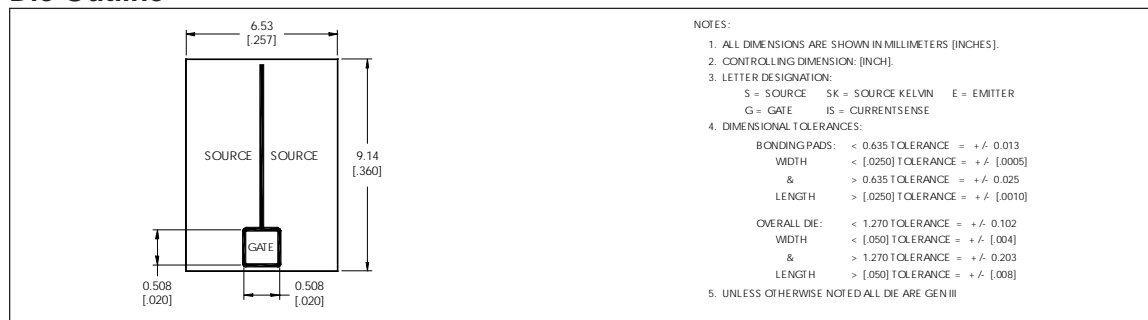
Electrical Characteristics *

Parameter	Description	Min	Typ.	Max	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	75V	—	—	$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$ ***	Static Drain-to-Source On-Resistance	—	2.5m Ω	4.5m Ω	$V_{GS} = 10V, I_D = 110A$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20 μA	$V_{DS} = 75V, V_{GS} = 0V, T_J = 25^\circ C$
I_{GSS}	Gate-to-Source Leakage Current	—	—	$\pm 200nA$	$V_{GS} = \pm 20V$
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 $^\circ C$ to 175 $^\circ C$ Max.			

Mechanical Data

Nominal Back Metal Composition, Thickness:	Cr-NiV-Ag (1kA°-2kA°-5kA°)
Nominal Front Metal Composition, Thickness:	100% Al (0.008 mm)
Dimensions:	.257" x .360" [6.53 mm x 9.14 mm]
Wafer Diameter:	150 mm, with 100 flat
Wafer Thickness:	0.254 mm \pm 0.025 mm
Relevant Die Mechanical Drawing Number	01-5403
Minimum Street Width	0.107 mm
Reject Ink Dot Size	0.51 mm Diameter Minimum
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination
Recommended Die Attach Conditions:	For optimum electrical results, die attach temperature should not exceed 300 $^\circ C$
Reference Packaged Part	IRFP2907

Die Outline



* Electrical characteristics are reported for the reference packaged part (see above) and can not be guaranteed in die sales form. Variations in customer packaging materials, dimensions and processes may affect parametric performance.

** Contact factory for these product forms.

***The typical $R_{DS(on)}$ is an estimated value for the bare die, actual results will depend on customer packaging materials and dimensions.